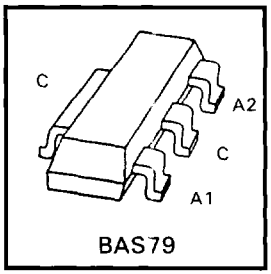
SILICON PLANAR DUAL HIGH VOLTAGE SWITCHING DIODES IN SOT89 AND SOT223 PACKAGES

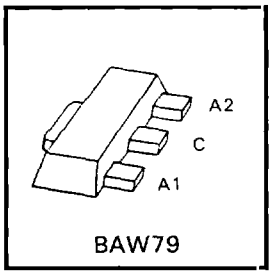
BAS79A-D (SOT223)
BAW79A-D (SOT89)

PARTMARKING DETAIL
BAW79A – GE
BAW79B – GF
BAW79C – GG
BAW79D – GH

BAS79A ⎫
BAS79A ⎬ DEVICE TYPE IN
BAS79A ⎪ FULL
BAS79A ⎭



BAS79



BAW79

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	BAW79A BAS79A	BAW79B BAS79B	BAW79C BAS79C	BAW79D BAS79D	UNIT
REVERSE VOLTAGE	V_R	50	100	200	400	V
PEAK REVERSE VOLTAGE	V_{RM}	50	100	200	400	V
FORWARD CURRENT	I_F	1	1	1	1	A
PEAK FORWARD CURRENT	I_{FM}	1	1	1	1	A
SURGE FORWARD CURRENT	I_{FS}	10	10	10	10	A
TOTAL POWER DISSIPATION (SOT89)	P_{tot}	1.0	1.0	1.0	1.0	W
TOTAL POWER DISSIPATION(SOT223)	P_{tot}	1.5	1.5	1.5	1.5	W
JUNCTION AND STORAGE TEMPERATURE RANGE	T_j:T_{stg}	-65 to +150				°C

ELECTRICAL CHARACTERISTICS (at T_{amb}=25°C unless otherwise stated)

PARAMETER		SYMBOL	MIN	TYPE	MAX	UNIT	
BREAKDOWN VOLTAGE	A	$V_{(BR)}$	50	-	-	V	$I_{(BR)}$=100mA
	B		100	-	-	V	
BAS\BAW79	C		200	-	-	V	
	D		400	-	-	V	
FORWARD VOLTAGE		V_F	-	-	1.6	V	I_F=1A
			-	-	2.0	V	I_F=1A
REVERSE CURRENT		I_R	-	-	1	μA	V_R=V_{RMAX}
			-	-	50	μA	V_R=V_{RMAX},T_A=150°C
DIODE CAPACITANCE		C_D	-	10	-	pF	V_R=0, f=1MHz
REVERSE RECOVERY TIME		t_{rr}	-	1	-	μS	I_F=200mA I_R=200mA R_L=100W measured at I_R=20mA